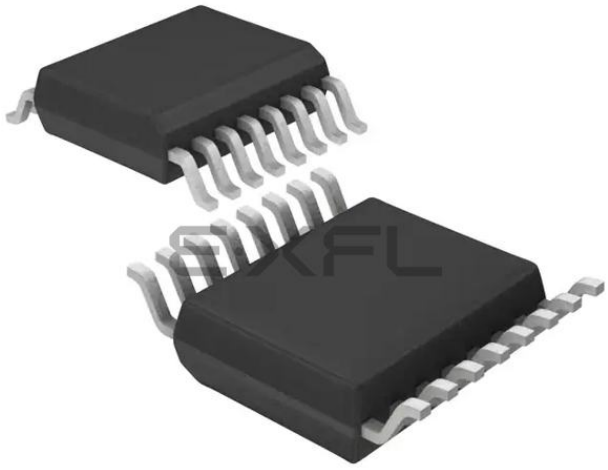

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	S08
Core Size	8-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SPI, UART/USART
Peripherals	LVD, POR, PWM, WDT
Number of I/O	14
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	256 x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 12x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	16-TSSOP (0.173", 4.40mm Width)
Supplier Device Package	16-TSSOP
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc9s08pa16avtgr

- Input/Output
  - Up to 37 GPIOs including one output-only pin
  - One 8-bit keyboard interrupt module (KBI)
  - Two true open-drain output pins
  - Four, ultra-high current sink pins supporting 20 mA source/sink current
- Package options
  - 44-pin LQFP
  - 32-pin LQFP
  - 20-pin SOIC; 20-pin TSSOP
  - 16-pin TSSOP

4 Ratings

4.1 Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T_{STG}	Storage temperature	–55	150	°C	1
T_{SDR}	Solder temperature, lead-free	—	260	°C	2

1. Determined according to JEDEC Standard JESD22-A103, *High Temperature Storage Life*.
2. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human body model	-6000	+6000	V	1
V_{CDM}	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
I_{LAT}	Latch-up current at ambient temperature of 105°C	-100	+100	mA	

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.

4.4 Voltage and current operating ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in below table may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this document.

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, either V_{SS} or V_{DD}) or the programmable pullup resistor associated with the pin is enabled.

Symbol	Description	Min.	Max.	Unit
V_{DD}	Supply voltage	–0.3	6.0	V
I_{DD}	Maximum current into V_{DD}	—	120	mA
V_{DIO}	Digital input voltage (except $\overline{\text{RESET}}$, EXTAL, XTAL, or true open drain pin PTA2 and PTA3)	–0.3	V_{DD} + 0.3	V
	Digital input voltage (true open drain pin PTA2 and PTA3)	-0.3	6	V
V_{AIO}	Analog[1], $\overline{\text{RESET}}$, EXTAL, and XTAL input voltage	–0.3	V_{DD} + 0.3	V
I_D	Instantaneous maximum current single pin limit (applies to all port pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V

1. All digital I/O pins, except open-drain pin PTA2 and PTA3, are internally clamped to V_{SS} and V_{DD}. PTA2 and PTA3 is only clamped to V_{SS}.

5 General

5.1 Nonswitching electrical specifications

5.1.1 DC characteristics

This section includes information about power supply requirements and I/O pin characteristics.

Table 2. DC characteristics

Symbol	C	Descriptions			Min	Typical[1]	Max	Unit
—	—	Operating voltage		—	2.7	—	5.5	V
V_{OH}	C	Output high voltage	All I/O pins, standard-drive strength	5 V, I_{load} = -5 mA	V_{DD} - 0.8	—	—	V
	C			3 V, I_{load} = -2.5 mA	V_{DD} - 0.8	—	—	V
	C		High current drive pins, high-drive strength[2]	5 V, I_{load} = -20 mA	V_{DD} - 0.8	—	—	V
	C			3 V, I_{load} = -10 mA	V_{DD} - 0.8	—	—	V

Table continues on the next page...

Table 2. DC characteristics (continued)

Symbol	C	Descriptions			Min	Typical[1]	Max	Unit
I_{OHT}	D	Output high current	Max total I_{OH} for all ports	5 V	—	—	-100	mA
				3 V	—	—	-50	
V_{OL}	C	Output low voltage	All I/O pins, standard-drive strength	5 V, I_{load} = 5 mA	—	—	0.8	V
	C			3 V, I_{load} = 2.5 mA	—	—	0.8	V
	C		High current drive pins, high-drive strength[2]	5 V, I_{load} =20 mA	—	—	0.8	V
	C			3 V, I_{load} = 10 mA	—	—	0.8	V
I_{OLT}	D	Output low current	Max total I_{OL} for all ports	5 V	—	—	100	mA
				3 V	—	—	50	
V_{IH}	P	Input high voltage	All digital inputs	V_{DD}>4.5V	0.70 × V_{DD}	—	—	V
	C			V_{DD}>2.7V	0.75 × V_{DD}	—	—	
V_{IL}	P	Input low voltage	All digital inputs	V_{DD}>4.5V	—	—	0.30 × V_{DD}	V
	C			V_{DD}>2.7V	—	—	0.35 × V_{DD}	
V_{hys}	C	Input hysteresis	All digital inputs	—	0.06 × V_{DD}	—	—	mV
$\lvert I_{In}\rvert$	P	Input leakage current	All input only pins (per pin)	V_{IN} = V_{DD} or V_{SS}	—	0.1	1	µA
$\lvert I_{OZ}\rvert$	P	Hi-Z (off-state) leakage current	All input/output (per pin)	V_{IN} = V_{DD} or V_{SS}	—	0.1	1	µA
$\lvert I_{OZTOT}\rvert$	C	Total leakage combined for all inputs and Hi-Z pins	All input only and I/O	V_{IN} = V_{DD} or V_{SS}	—	—	2	µA
R_{PU}	P	Pullup resistors	All digital inputs, when enabled (all I/O pins other than PTA2 and PTA3)	—	30.0	—	50.0	kΩ
R_{PU}[3]	P	Pullup resistors	PTA2 and PTA3 pin	—	30.0	—	60.0	kΩ
I_{IC}	D	DC injection current[4, 5, 6]	Single pin limit	V_{IN} < V_{SS}, V_{IN} > V_{DD}	-0.2	—	2	mA
			Total MCU limit, includes sum of all stressed pins		-5	—	25	
C_{In}	C	Input capacitance, all pins		—	—	—	7	pF
V_{RAM}	C	RAM retention voltage		—	2.0	—	—	V

1. Typical values are measured at 25 °C. Characterized, not tested.
2. Only PTB4, PTB5, PTD0, PTD1 support ultra high current output.
3. The specified resistor value is the actual value internal to the device. The pullup value may appear higher when measured externally on the pin.
4. All functional non-supply pins, except for , are internally clamped to V_{SS} and V_{DD}.
5. Input must be current-limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the large one.

6. Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If the positive injection current ($V_{In} > V_{DD}$) is higher than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure that external V_{DD} load will shunt current higher than maximum injection current when the MCU is not consuming power, such as no system clock is present, or clock rate is very low (which would reduce overall power consumption).

Table 3. LVD and POR Specification

Symbol	C	Description		Min	Typ	Max	Unit
V_{POR}	D	POR re-arm voltage[1, 2]		1.5	1.75	2.0	V
V_{LVDH}	C	Falling low-voltage detect threshold - high range (LVDV = 1)[3]		4.2	4.3	4.4	V
V_{LVW1H}	C	Falling low-voltage warning threshold - high range	Level 1 falling (LVWV = 00)	4.3	4.4	4.5	V
V_{LVW2H}	C		Level 2 falling (LVWV = 01)	4.5	4.5	4.6	V
V_{LVW3H}	C		Level 3 falling (LVWV = 10)	4.6	4.6	4.7	V
V_{LVW4H}	C		Level 4 falling (LVWV = 11)	4.7	4.7	4.8	V
V_{HYSH}	C	High range low-voltage detect/warning hysteresis		—	100	—	mV
V_{LVDL}	C	Falling low-voltage detect threshold - low range (LVDV = 0)		2.56	2.61	2.66	V
V_{LVDW1L}	C	Falling low-voltage warning threshold - low range	Level 1 falling (LVWV = 00)	2.62	2.7	2.78	V
V_{LVDW2L}	C		Level 2 falling (LVWV = 01)	2.72	2.8	2.88	V
V_{LVDW3L}	C		Level 3 falling (LVWV = 10)	2.82	2.9	2.98	V
V_{LVDW4L}	C		Level 4 falling (LVWV = 11)	2.92	3.0	3.08	V
V_{HYSDL}	C	Low range low-voltage detect hysteresis		—	40	—	mV
V_{HYSWL}	C	Low range low-voltage warning hysteresis		—	80	—	mV
V_{BG}	P	Buffered bandgap output [4]		1.14	1.16	1.18	V

1. Maximum is highest voltage that POR is guaranteed.
2. POR ramp time must be longer than 20us/V to get a stable startup.
3. Rising thresholds are falling threshold + hysteresis.
4. Voltage factory trimmed at V_{DD} = 5.0 V, Temp = 25 °C

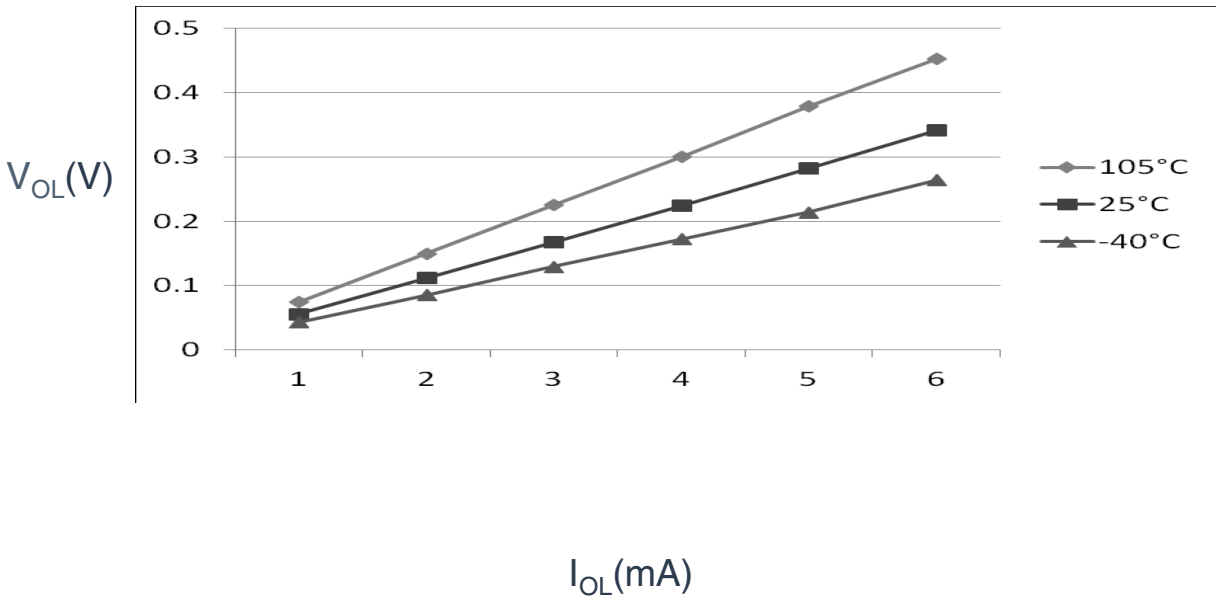


Figure 5. Typical I_{OL} Vs. V_{OL} (standard drive strength) (V_{DD} = 5 V)

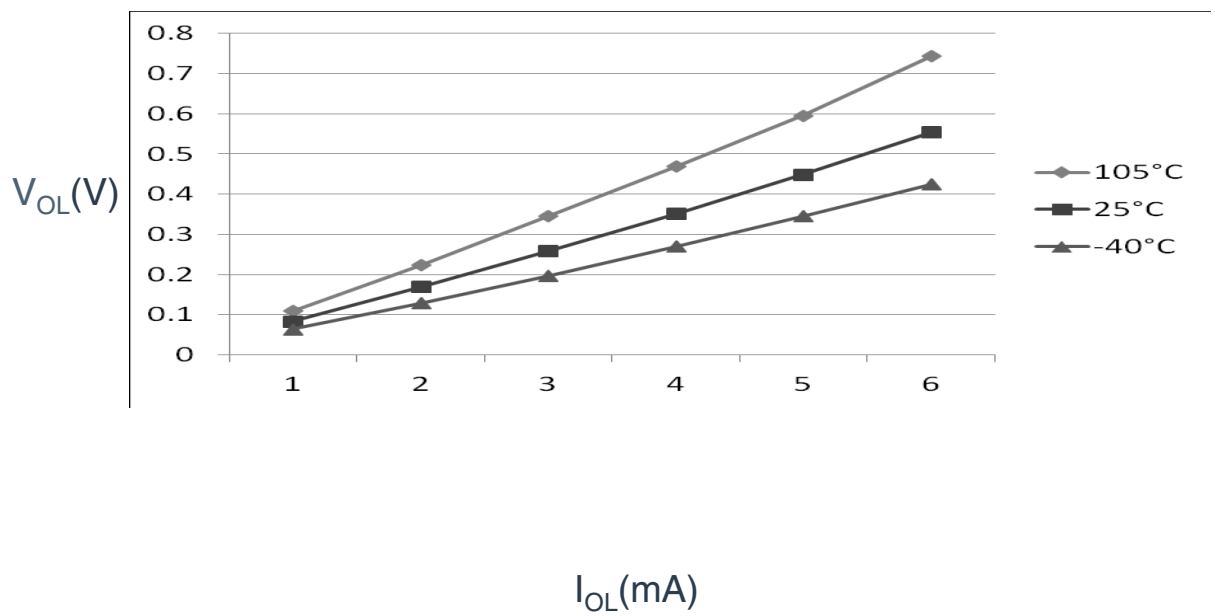


Figure 6. Typical I_{OL} Vs. V_{OL} (standard drive strength) (V_{DD} = 3 V)

5.1.2 Supply current characteristics

This section includes information about power supply current in various operating modes.

Table 4. Supply current characteristics

Num	C	Parameter	Symbol	Bus Freq	V_{DD} (V)	Typical[1]	Max	Unit	Temp
1	C	Run supply current FEI mode, all modules on; run from flash	RI_{DD}	20 MHz	5	7.60	—	mA	-40 to 105 °C
	C			10 MHz		4.65	—		
				1 MHz		1.90	—		
	C			20 MHz	3	7.05	—		
	C			10 MHz		4.40	—		
				1 MHz		1.85	—		
2	C	Run supply current FEI mode, all modules off & gated; run from flash	RI_{DD}	20 MHz	5	5.88	—	mA	-40 to 105 °C
	C			10 MHz		3.70	—		
				1 MHz		1.85	—		
	C			20 MHz	3	5.35	—		
	C			10 MHz		3.42	—		
				1 MHz		1.80	—		
3	P	Run supply current FBE mode, all modules on; run from RAM	RI_{DD}	20 MHz	5	10.9	14.0	mA	-40 to 105 °C
	C			10 MHz		6.10	—		
				1 MHz		1.69	—		
	P			20 MHz	3	8.18	—		
	C			10 MHz		5.14	—		
				1 MHz		1.44	—		
4	P	Run supply current FBE mode, all modules off & gated; run from RAM	RI_{DD}	20 MHz	5	8.50	13.0	mA	-40 to 105 °C
	C			10 MHz		5.07	—		
				1 MHz		1.59	—		
	P			20 MHz	3	6.11	—		
	C			10 MHz		4.10	—		
				1 MHz		1.34	—		
5	P	Wait mode current FEI mode, all modules on	WI_{DD}	20 MHz	5	5.95	—	mA	-40 to 105 °C
	C			10 MHz		3.50	—		
				1 MHz		1.24	—		
	C			20 MHz	3	5.45	—		
				10 MHz		3.25	—		
				1 MHz		1.20	—		
6	C	Stop3 mode supply current no clocks active (except 1kHz LPO clock)[2, 3]	$S3I_{DD}$	—	5	4.6	—	µA	-40 to 105 °C
	C			—	3	4.5	—		-40 to 105 °C
7	C	ADC adder to stop3	—	—	5	40	—	µA	-40 to 105 °C

Table continues on the next page...

Table 4. Supply current characteristics (continued)

Num	C	Parameter	Symbol	Bus Freq	V_{DD} (V)	Typical[1]	Max	Unit	Temp
	C	ADLPC = 1 ADLSMP = 1 ADCO = 1 MODE = 10B ADICLK = 11B			3	39	—		
8	C	LVD adder to stop3[4]	—	—	5	128	—	µA	-40 to 105 °C
	C				3	124	—		

1. Data in Typical column was characterized at 5.0 V, 25 °C or is typical recommended value.
2. RTC adder cause <1 µA I_{DD} increase typically, RTC clock source is 1kHz LPO clock.
3. ACMP adder cause <10 µA I_{DD} increase typically.
4. LVD is periodically woken up from stop3 by 5% duty cycle. The period is equal to or less than 2 ms.

5.1.3 EMC performance

Electromagnetic compatibility (EMC) performance is highly dependent on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation all play a significant role in EMC performance. The system designer should consult Freescale applications notes such as AN2321, AN1050, AN1263, AN2764, and AN1259 for advice and guidance specifically targeted at optimizing EMC performance.

5.1.3.1 EMC radiated emissions operating behaviors

Table 5. EMC radiated emissions operating behaviors for 44-pin LQFP package

Symbol	Description	Frequency band (MHz)	Typ.	Unit	Notes
V_{RE1}	Radiated emissions voltage, band 1	0.15–50	8	dBµV	1, 2
V_{RE2}	Radiated emissions voltage, band 2	50–150	8	dBµV	
V_{RE3}	Radiated emissions voltage, band 3	150–500	8	dBµV	
V_{RE4}	Radiated emissions voltage, band 4	500–1000	5	dBµV	
V_{RE_IEC}	IEC level	0.15–1000	N	—	2, 3

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*. Measurements were made while the microcontroller was running basic application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.
2. V_{DD} = 5.0 V, T_A = 25 °C, f_{OSC} = 10 MHz (crystal), f_{SYS} = 20 MHz, f_{BUS} = 20 MHz
3. Specified according to Annex D of IEC Standard 61967-2, *Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*

5.2 Switching specifications

5.2.1 Control timing

Table 6. Control timing

Num	C	Rating		Symbol	Min	Typical[1]	Max	Unit
1	P	Bus frequency ($t_{cyc} = 1/f_{Bus}$)		f_{Bus}	DC	—	20	MHz
2	C	Internal low power oscillator frequency		f_{LPO}	—	1.0	—	KHz
3	D	External reset pulse width[2]		t_{extrst}	1.5 × t_{cyc}	—	—	ns
4	D	Reset low drive		t_{rstdrv}	34 × t_{cyc}	—	—	ns
5	D	BKGD/MS setup time after issuing background debug force reset to enter user or BDM modes		t_{MSSU}	500	—	—	ns
6	D	BKGD/MS hold time after issuing background debug force reset to enter user or BDM modes[3]		t_{MSH}	100	—	—	ns
7	D	IRQ pulse width	Asynchronous path[2]	t_{ILIH}	100	—	—	ns
	D		Synchronous path[4]	t_{IHIL}	1.5 × t_{cyc}	—	—	ns
8	D	Keyboard interrupt pulse width	Asynchronous path[2]	t_{ILIH}	100	—	—	ns
	D		Synchronous path	t_{IHIL}	1.5 × t_{cyc}	—	—	ns
9	C	Port rise and fall time - standard drive strength (load = 50 pF)[5]	—	t_{Rise}	—	10.2	—	ns
	C			t_{Fall}	—	9.5	—	ns
	C	Port rise and fall time - high drive strength (load = 50 pF)[5]	—	t_{Rise}	—	5.4	—	ns
	C			t_{Fall}	—	4.6	—	ns

1. Typical values are based on characterization data at V_{DD} = 5.0 V, 25 °C unless otherwise stated.
2. This is the shortest pulse that is guaranteed to be recognized as a reset pin request.
3. To enter BDM mode following a POR, BKGD/MS must be held low during the powerup and for a hold time of t_{MSH} after V_{DD} rises above V_{LVD}.
4. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized.
5. Timing is shown with respect to 20% V_{DD} and 80% V_{DD} levels. Temperature range -40 °C to 105 °C.

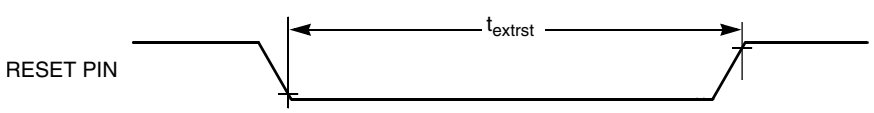


Figure 9. Reset timing

6.1 External oscillator (XOSC) and ICS characteristics

Table 10. XOSC and ICS specifications (temperature range = -40 to 105 °C ambient)

Num	C	Characteristic		Symbol	Min	Typical[1]	Max	Unit
1	C	Oscillator crystal or resonator	Low range (RANGE = 0)	f_{lo}	31.25	32.768	39.0625	kHz
	C		High range (RANGE = 1) FEE or FBE mode[2]	f_{hi}	4	—	20	MHz
	C		High range (RANGE = 1), high gain (HGO = 1), FBELP mode	f_{hi}	4	—	20	MHz
	C		High range (RANGE = 1), low power (HGO = 0), FBELP mode	f_{hi}	4	—	20	MHz
2	D	Load capacitors		C1, C2	See Note[3]			
3	D	Feedback resistor	Low Frequency, Low-Power Mode[4]	R_F	—	—	—	MΩ
			Low Frequency, High-Gain Mode		—	10	—	MΩ
			High Frequency, Low-Power Mode		—	1	—	MΩ
			High Frequency, High-Gain Mode		—	1	—	MΩ
4	D	Series resistor - Low Frequency	Low-Power Mode [4]	R_S	—	—	—	kΩ
			High-Gain Mode		—	200	—	kΩ
5	D	Series resistor - High Frequency	Low-Power Mode[4]	R_S	—	—	—	kΩ
	D	Series resistor - High Frequency, High-Gain Mode	4 MHz		—	0	—	kΩ
	D		8 MHz		—	0	—	kΩ
	D		16 MHz		—	0	—	kΩ
6	C	Crystal start-up time Low range = 32.768 kHz crystal; High range = 20 MHz crystal[5, 6]	Low range, low power	t_{CSTL}	—	1000	—	ms
	C		Low range, high power		—	800	—	ms
	C		High range, low power	t_{CSTH}	—	3	—	ms
	C		High range, high power		—	1.5	—	ms
7	T	Internal reference start-up time		t_{IRST}	—	20	50	µs
8	D	Square wave input clock frequency	FEE or FBE mode[2]	f_{extal}	0.03125	—	5	MHz
	D		FBELP mode		0	—	20	MHz
9	P	Average internal reference frequency - trimmed		f_{int_t}	—	31.25	—	kHz
10	P	DCO output frequency range - trimmed		f_{dco_t}	16	—	20	MHz
11	P	Total deviation of DCO output from trimmed frequency[5]	Over full voltage and temperature range	Δf_{dco_t}	—	—	±2.0	$\%f_{dco}$
	C		Over fixed voltage and temperature range of 0 to 70 °C				±1.0	
12	C	FLL acquisition time[5, 7]		$t_{Acquire}$	—	—	2	ms

Table continues on the next page...

Table 10. XOSC and ICS specifications (temperature range = -40 to 105 °C ambient) (continued)

Num	C	Characteristic	Symbol	Min	Typical[1]	Max	Unit
13	C	Long term jitter of DCO output clock (averaged over 2 ms interval)[8]	C_{Jitter}	—	0.02	0.2	$\%f_{dco}$

1. Data in Typical column was characterized at 5.0 V, 25 °C or is typical recommended value.
2. When ICS is configured for FEE or FBE mode, input clock source must be divisible using RDIV to within the range of 31.25 kHz to 39.0625 kHz.
3. See crystal or resonator manufacturer's recommendation.
4. Load capacitors (C_1,C_2), feedback resistor (R_F) and series resistor (R_S) are incorporated internally when RANGE = HGO = 0.
5. This parameter is characterized and not tested on each device.
6. Proper PC board layout procedures must be followed to achieve specifications.
7. This specification applies to any time the FLL reference source or reference divider is changed, trim value changed, or changing from FLL disabled (FBELP, FBILP) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
8. Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{Bus}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the FLL circuitry via V_{DD} and V_{SS} and variation in crystal oscillator frequency increase the C_{Jitter} percentage for a given interval.

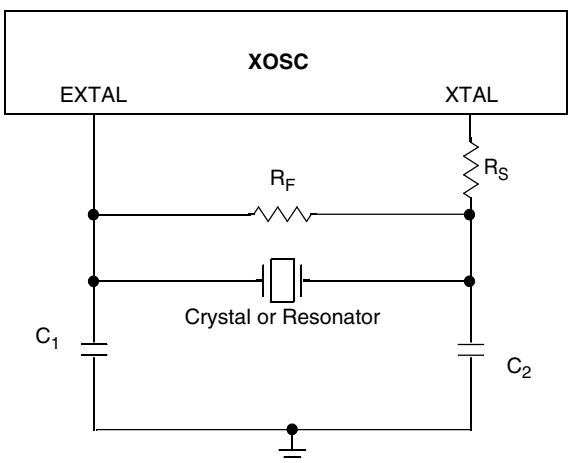


Figure 15. Typical crystal or resonator circuit

6.2 NVM specifications

This section provides details about program/erase times and program/erase endurance for the flash and EEPROM memories.

Table 11. Flash characteristics

C	Characteristic	Symbol	Min[1]	Typical[2]	Max[3]	Unit[4]
D	Supply voltage for program/erase -40 °C to 105 °C	$V_{prog/erase}$	2.7	—	5.5	V
D	Supply voltage for read operation	V_{Read}	2.7	—	5.5	V

Table continues on the next page...

Table 11. Flash characteristics (continued)

C	Characteristic	Symbol	Min[1]	Typical[2]	Max[3]	Unit[4]
D	NVM Bus frequency	f_{NVMBUS}	1	—	25	MHz
D	NVM Operating frequency	f_{NVMOP}	0.8	1	1.05	MHz
D	Erase Verify All Blocks	t_{VFYALL}	—	—	17338	t_{cyc}
D	Erase Verify Flash Block	t_{RD1BLK}	—	—	16913	t_{cyc}
D	Erase Verify EEPROM Block	t_{RD1BLK}	—	—	810	t_{cyc}
D	Erase Verify Flash Section	t_{RD1SEC}	—	—	484	t_{cyc}
D	Erase Verify EEPROM Section	$t_{DRD1SEC}$	—	—	555	t_{cyc}
D	Read Once	t_{RDONCE}	—	—	450	t_{cyc}
D	Program Flash (2 word)	t_{PGM2}	0.12	0.12	0.29	ms
D	Program Flash (4 word)	t_{PGM4}	0.20	0.21	0.46	ms
D	Program Once	$t_{PGMONCE}$	0.20	0.21	0.21	ms
D	Program EEPROM (1 Byte)	t_{DPGM1}	0.10	0.10	0.27	ms
D	Program EEPROM (2 Byte)	t_{DPGM2}	0.17	0.18	0.43	ms
D	Program EEPROM (3 Byte)	t_{DPGM3}	0.25	0.26	0.60	ms
D	Program EEPROM (4 Byte)	t_{DPGM4}	0.32	0.33	0.77	ms
D	Erase All Blocks	t_{ERSALL}	96.01	100.78	101.49	ms
D	Erase Flash Block	t_{ERSBLK}	95.98	100.75	101.44	ms
D	Erase Flash Sector	t_{ERSPG}	19.10	20.05	20.08	ms
D	Erase EEPROM Sector	t_{DERSPG}	4.81	5.05	20.57	ms
D	Unsecure Flash	t_{UNSECU}	96.01	100.78	101.48	ms
D	Verify Backdoor Access Key	t_{VFYKEY}	—	—	464	t_{cyc}
D	Set User Margin Level	t_{MLOADU}	—	—	407	t_{cyc}
C	FLASH Program/erase endurance T_L to T_H = -40 °C to 105 °C	n_{FLPE}	10 k	100 k	—	Cycles
C	EEPROM Program/erase endurance TL to TH = -40 °C to 105 °C	n_{FLPE}	50 k	500 k	—	Cycles
C	Data retention at an average junction temperature of T_{Javg} = 85°C after up to 10,000 program/erase cycles	t_{D_ret}	15	100	—	years

1. Minimum times are based on maximum f_{NVMOP} and maximum f_{NVMBUS}
2. Typical times are based on typical f_{NVMOP} and maximum f_{NVMBUS}
3. Maximum times are based on typical f_{NVMOP} and typical f_{NVMBUS} plus aging
4. $t_{cyc} = 1 / f_{NVMBUS}$

Program and erase operations do not require any special power sources other than the normal V_{DD} supply. For more detailed information about program/erase operations, see the Memory section.

6.3 Analog

6.3.1 ADC characteristics

Table 12. 5 V 12-bit ADC operating conditions

Characteristic	Conditions	Symb	Min	Typ[1]	Max	Unit	Comment
Supply voltage	Absolute	V_{DDA}	2.7	—	5.5	V	—
	Delta to V_{DD} (V_{DD}-V_{DDAD})	ΔV_{DDA}	-100	0	+100	mV	
Ground voltage	Delta to V_{SS} (V_{SS}-V_{SSA})[2]	ΔV_{SSA}	-100	0	+100	mV	
Input voltage		V_{ADIN}	V_{REFL}	—	V_{REFH}	V	
Input capacitance		C_{ADIN}	—	4.5	5.5	pF	
Input resistance		R_{ADIN}	—	3	5	kΩ	—
Analog source resistance	12-bit mode • f_{ADCK} > 4 MHz • f_{ADCK} < 4 MHz	R_{AS}	— —	— —	2 5	kΩ	External to MCU
	10-bit mode • f_{ADCK} > 4 MHz • f_{ADCK} < 4 MHz		— —	— —	5 10		
	8-bit mode (all valid f_{ADCK})		—	—	10		
ADC conversion clock frequency	High speed (ADLPC=0)	f_{ADCK}	0.4	—	8.0	MHz	—
	Low power (ADLPC=1)		0.4	—	4.0		

1. Typical values assume V_{DDA} = 5.0 V, Temp = 25°C, f_{ADCK}=1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
2. DC potential difference.

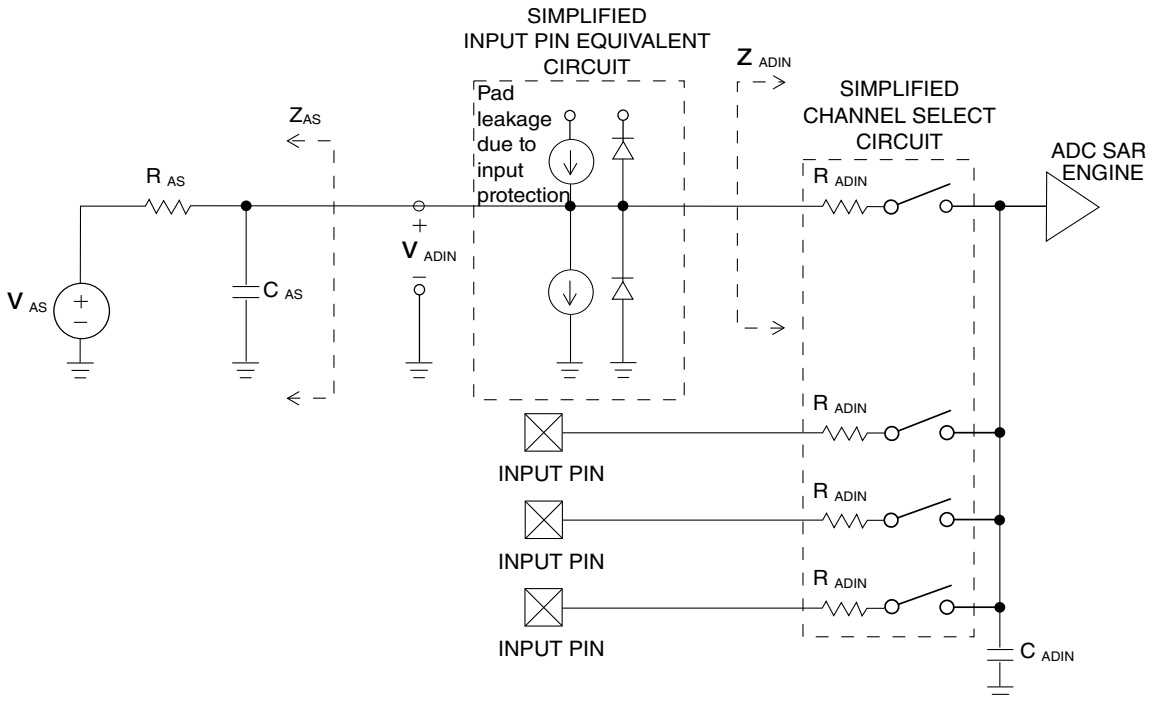


Figure 16. ADC input impedance equivalency diagram

Table 13. 12-bit ADC Characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA})

Characteristic	Conditions	C	Symb	Min	Typ[1]	Max	Unit
Supply current ADLPC = 1 ADLSMP = 1 ADCO = 1		T	I_{DDA}	—	133	—	µA
Supply current ADLPC = 1 ADLSMP = 0 ADCO = 1		T	I_{DDA}	—	218	—	µA
Supply current ADLPC = 0 ADLSMP = 1 ADCO = 1		T	I_{DDA}	—	327	—	µA
Supply current ADLPC = 0 ADLSMP = 0 ADCO = 1		T	I_{DDAD}	—	582	990	µA
Supply current	Stop, reset, module off	T	I_{DDA}	—	0.011	1	µA
ADC asynchronous clock source	High speed (ADLPC = 0)	P	f_{ADACK}	2	3.3	5	MHz

Table continues on the next page...

6.3.2 Analog comparator (ACMP) electricals

Table 14. Comparator electrical specifications

C	Characteristic	Symbol	Min	Typical	Max	Unit
D	Supply voltage	V_{DDA}	2.7	—	5.5	V
T	Supply current (Operation mode)	I_{DDA}	—	10	20	µA
D	Analog input voltage	V_{AIN}	V_{SS} - 0.3	—	V_{DDA}	V
P	Analog input offset voltage	V_{AIO}	—	—	40	mV
C	Analog comparator hysteresis (HYST=0)	V_H	—	15	20	mV
C	Analog comparator hysteresis (HYST=1)	V_H	—	20	30	mV
T	Supply current (Off mode)	I_{DDAOFF}	—	60	—	nA
C	Propagation Delay	t_D	—	0.4	1	µs

6.4 Communication interfaces

6.4.1 SPI switching specifications

The serial peripheral interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following tables provide timing characteristics for classic SPI timing modes. Refer to the SPI chapter of the chip's reference manual for information about the modified transfer formats used for communicating with slower peripheral devices. All timing is shown with respect to 20% V_{DD} and 70% V_{DD}, unless noted, and 100 pF load on all SPI pins. All timing assumes high drive strength is enabled for SPI output pins.

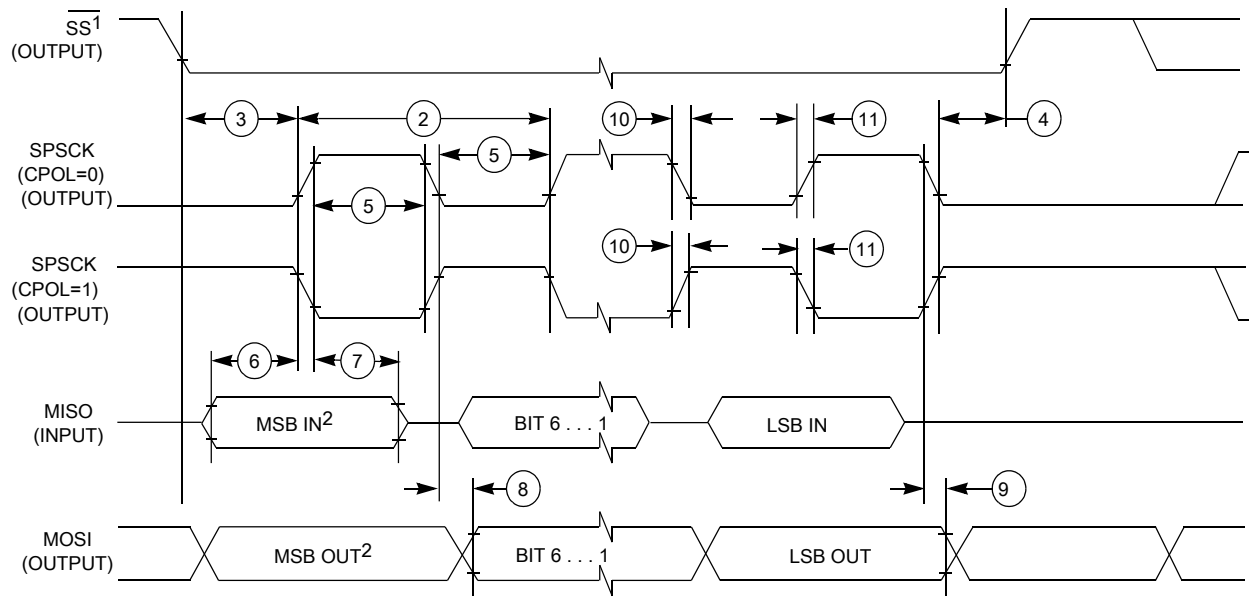
Table 15. SPI master mode timing

Num.	Symbol	Description	Min.	Max.	Unit	Comment
1	f_{op}	Frequency of operation	$f_{Bus}/2048$	$f_{Bus}/2$	Hz	f_{Bus} is the bus clock
2	t_{SPSCK}	SPSCK period	2 x t_{Bus}	2048 x t_{Bus}	ns	$t_{Bus} = 1/f_{Bus}$
3	t_{Lead}	Enable lead time	1/2	—	t_{SPSCK}	—
4	t_{Lag}	Enable lag time	1/2	—	t_{SPSCK}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{Bus} - 30	1024 x t_{Bus}	ns	—
6	t_{SU}	Data setup time (inputs)	15	—	ns	—
7	t_{HI}	Data hold time (inputs)	0	—	ns	—
8	t_v	Data valid (after SPSCK edge)	—	25	ns	—
9	t_{HO}	Data hold time (outputs)	0	—	ns	—
10	t_{RI}	Rise time input	—	t_{Bus} - 25	ns	—

Table continues on the next page...

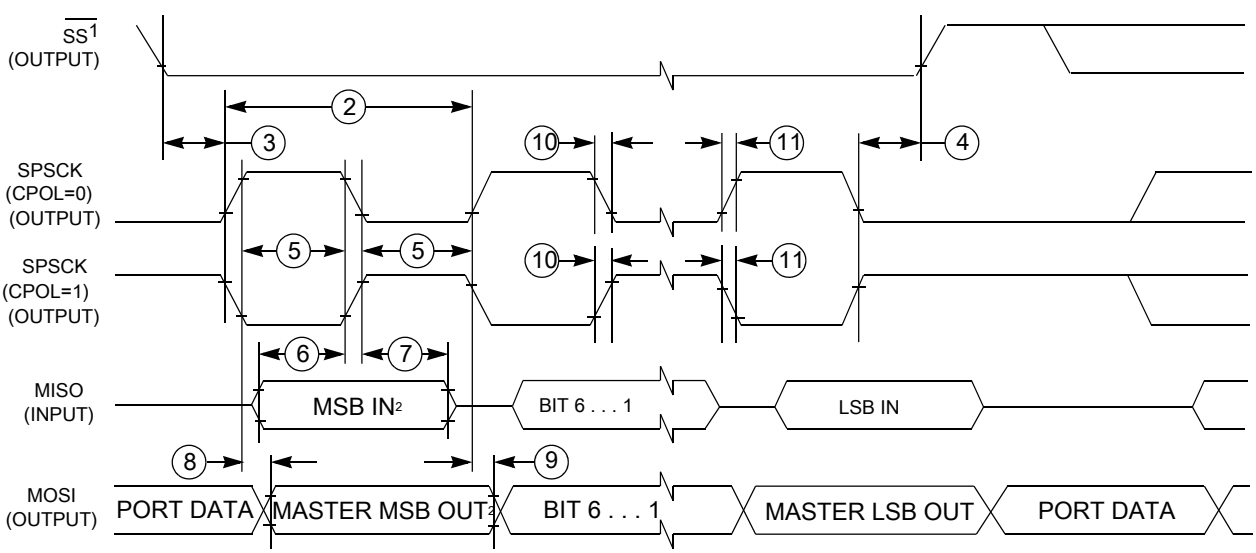
Table 15. SPI master mode timing (continued)

Num.	Symbol	Description	Min.	Max.	Unit	Comment
	t_{FI}	Fall time input				
11	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output				



1. If configured as an output.
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 17. SPI master mode timing (CPHA=0)



1.If configured as output
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 18. SPI master mode timing (CPHA=1)

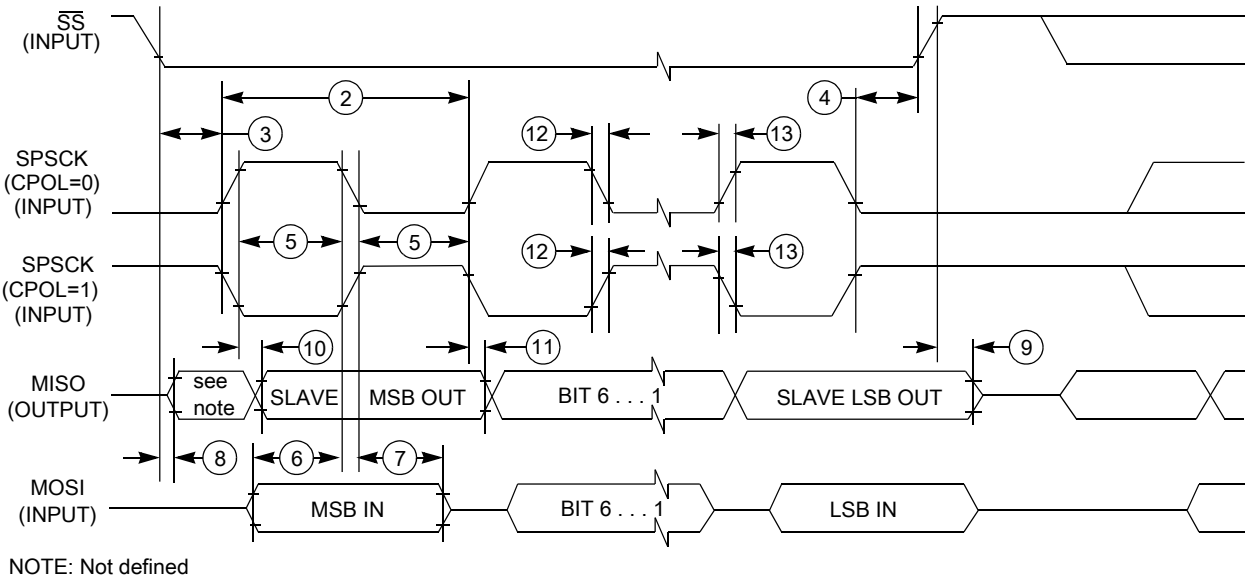


Figure 20. SPI slave mode timing (CPHA=1)

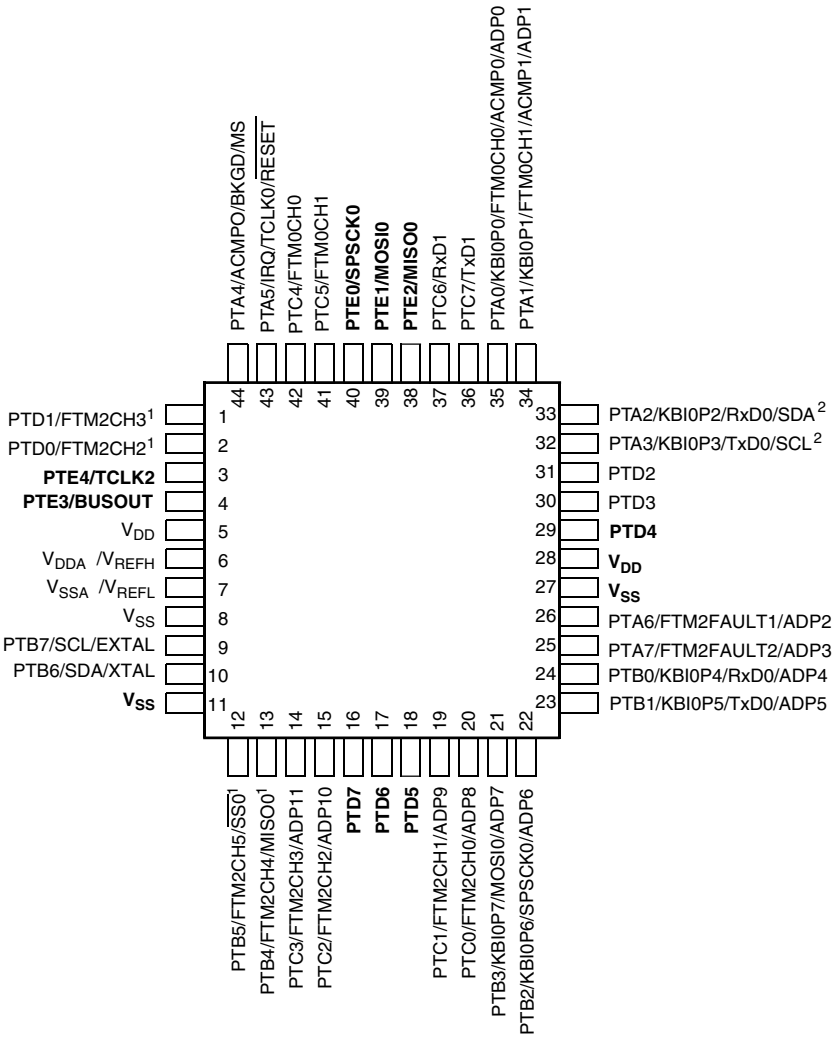
7 Dimensions

7.1 Obtaining package dimensions

Package dimensions are provided in package drawings.

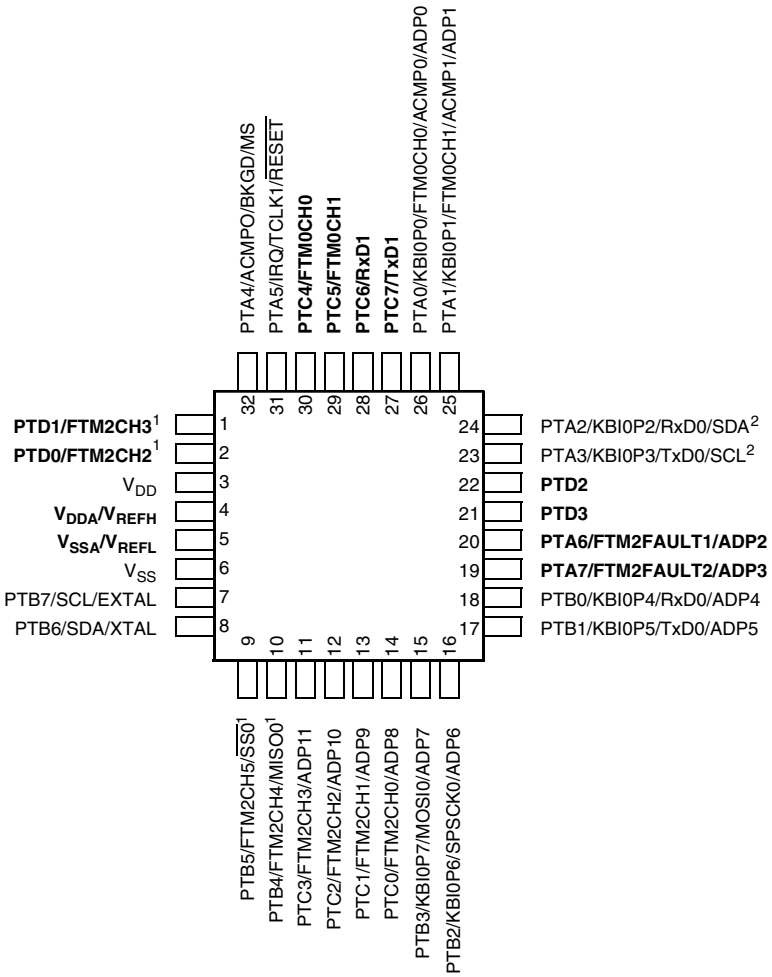
To find a package drawing, go to freescale.com and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
16-pin TSSOP	98ASH70247A
20-pin SOIC	98ASB42343B
20-pin TSSOP	98ASH70169A
32-pin LQFP	98ASH70029A
44-pin LQFP	98ASS23225W



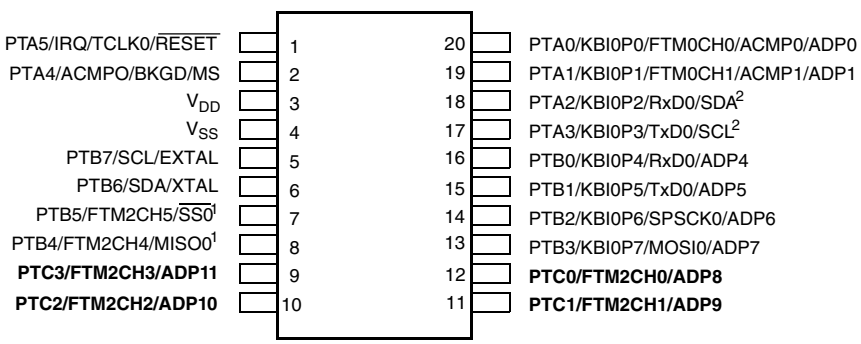
Pins in **bold** are not available on less pin-count packages.
1. High source/sink current pins
2. True open drain pins

Figure 21. MC9S08PA16 44-pin LQFP package



Pins in **bold** are not available on less pin-count packages.
1. High source/sink current pins
2. True open drain pins

Figure 22. MC9S08PA16 32-pin LQFP package



Pins in **bold** are not available on less pin-count packages.
1. High source/sink current pins
2. True open drain pins

Figure 23. MC9S08PA16 20-pin SOIC and TSSOP package

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